

**Eliminated hysteresis and stabilized power output over 20% in planar heterojunction perovskite solar cells by compositional and surface modifications to the low-temperature-processed TiO<sub>2</sub> layer**

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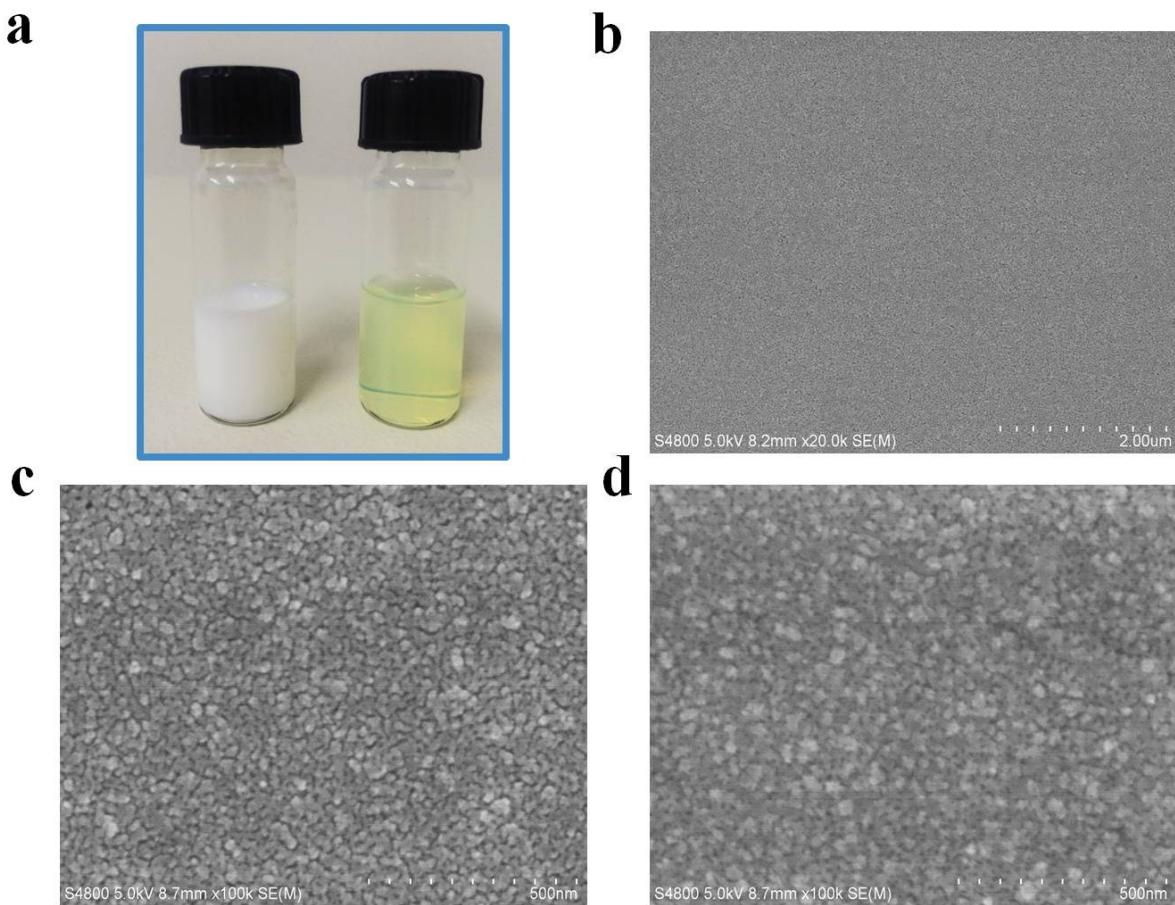
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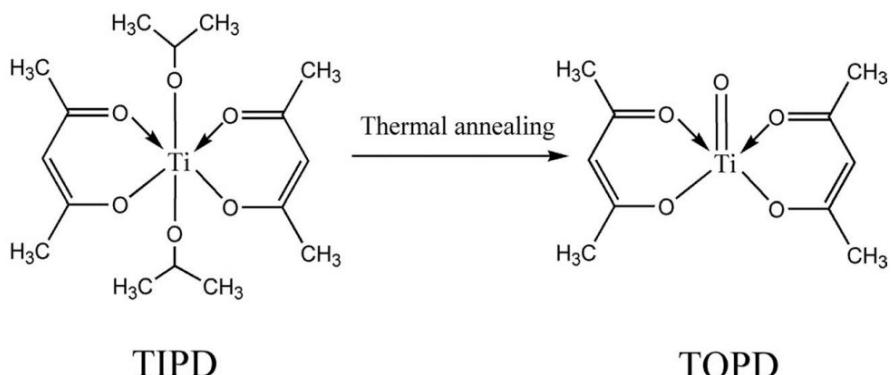
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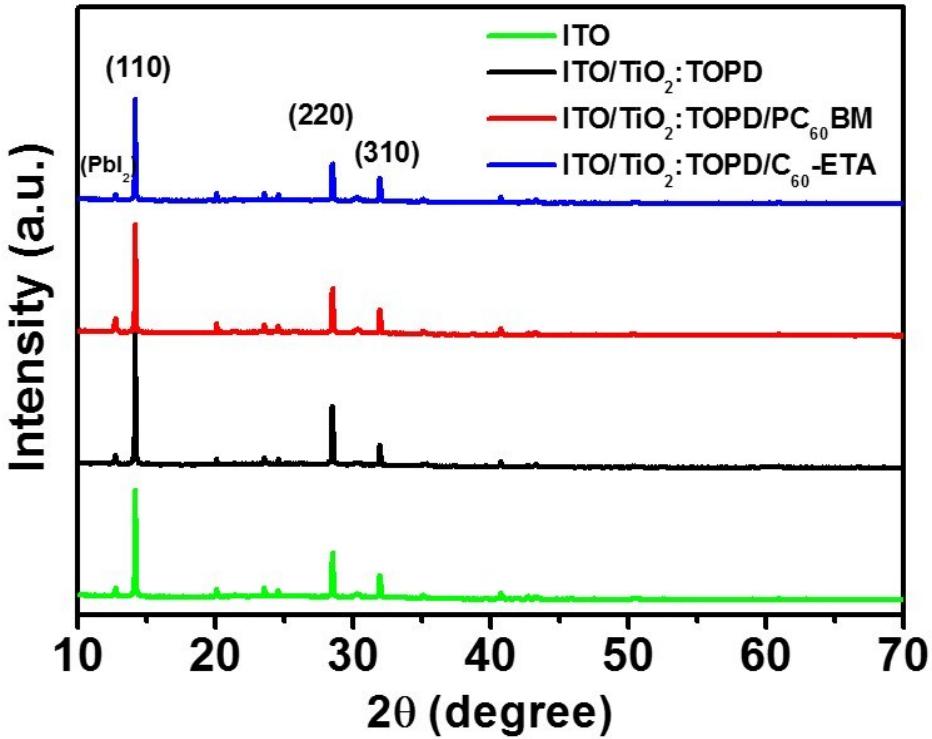
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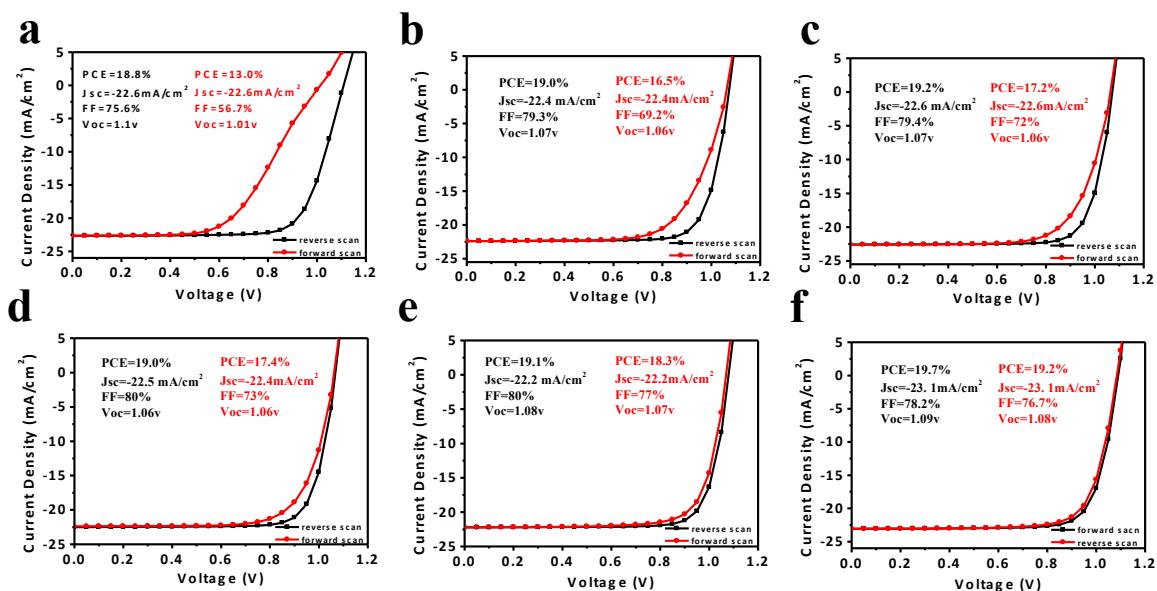
**Figure S1.** (a) Photos of the TiO<sub>2</sub> solution without (left) and with (right) the addition of TIPD. (b) Scanning electron microscopy (SEM) image of a TiO<sub>2</sub>:TOPD film cast on ITO substrate. High magnification SEM images of TiO<sub>2</sub> films cast on ITO substrate with (c) and without (d) the addition of TOPD.



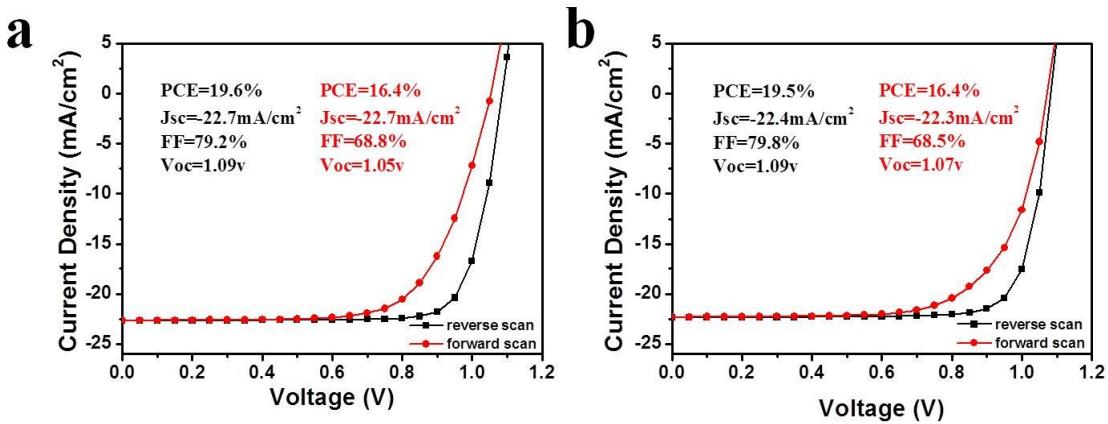
**Figure S2.** Conversion of TIPD to TOPD upon thermal annealing<sup>1,2</sup>.



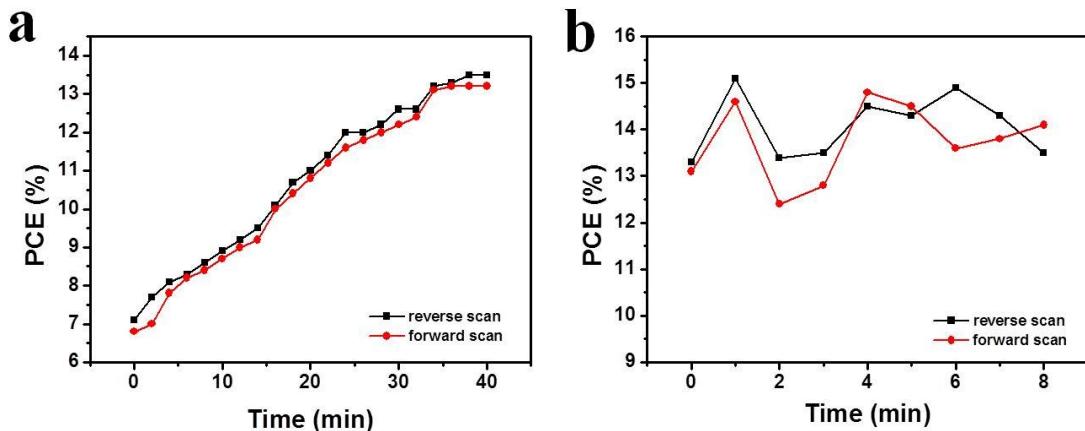
**Figure S3.** The XRD spectra of perovskite on ITO (green line), TiO<sub>2</sub>:TOPD (black line), TiO<sub>2</sub>:TOPD/PC<sub>60</sub>BM (red line), TiO<sub>2</sub>:TOPD/C<sub>60</sub>-ETA (blue line) surfaces.



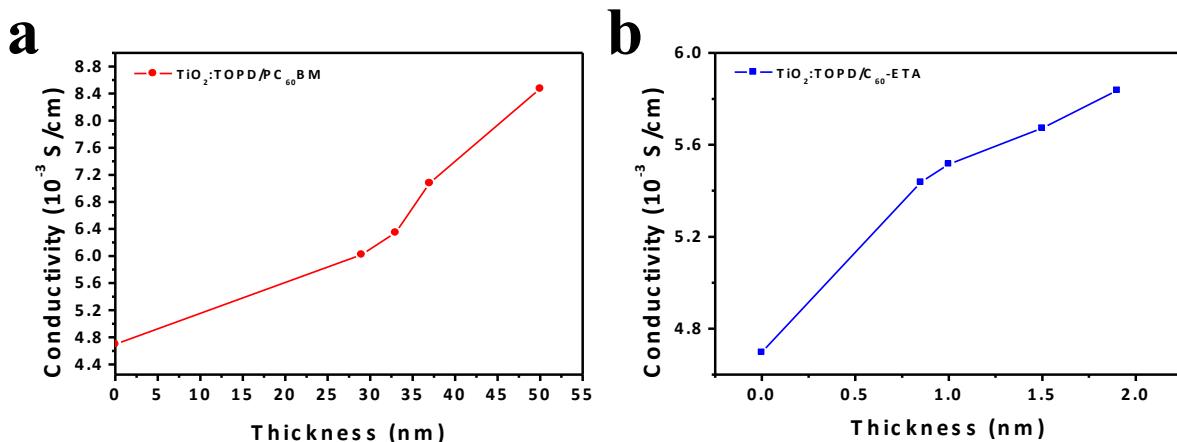
**Figure S4.** The *J-V* curves of devices using TiO<sub>2</sub>:TOPD/PC<sub>60</sub>BM as ETLs with (a) 0 nm, (b) 29 nm, (c) 33 nm, (d) 35 nm, (e) 37 nm, (f) 50 nm, respectively. PCEs close to the average values were selected and plotted in this figure.



**Figure S5.** The *J-V* curves of devices using (a) TiO<sub>2</sub>:TOPD/PC<sub>60</sub>BM(2nm) and (b) TiO<sub>2</sub>:TOPD/C<sub>60</sub>-ETA(2 nm) as ETLs, respectively. PCEs close to the average values were selected and plotted here.

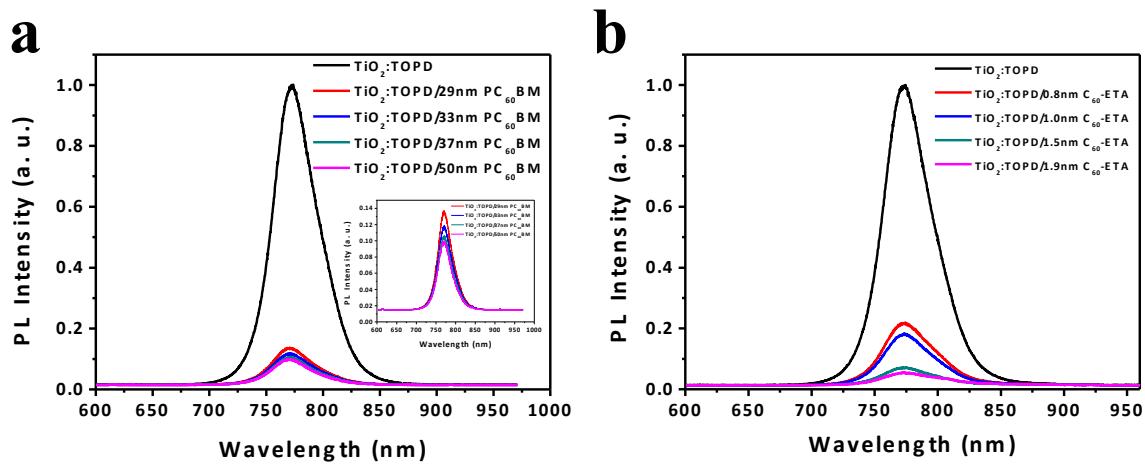


**Figure S6.** The evolutions of PCE as a function of illumination time using (a) 50 nm PC<sub>60</sub>BM and (b) 30 nm PC<sub>60</sub>BM as the ETLs.



**Figure S7.** (a) The conductivity of TiO<sub>2</sub>:TOPD/PC<sub>60</sub>BM films with various PC<sub>60</sub>BM thickness. (b) The

conductivity of  $\text{TiO}_2$ :TOPD/ $\text{C}_{60}$ -ETA films with various  $\text{C}_{60}$ -ETA thickness.



**Figure S8.** (a) The PL spectra of perovskite films on  $\text{TiO}_2$ :TOPD/ $\text{PC}_{60}$ BM with different  $\text{PC}_{60}$ BM thickness. (b) The PL spectra of perovskite films on  $\text{TiO}_2$ :TOPD/ $\text{C}_{60}$ -ETA with different  $\text{C}_{60}$ -ETA thickness.

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- [1] Z. A. Tan, W. Zhang, Z. Zhang, D. Qian, Y. Huang, J. Hou, Y. Li, *Adv. Mater.* **2012**, 24, 1476.  
 [2] Y. Yan, F. Cai, L. Yang, J. Li, Y. Zhang, F. Qin, C. Xiong, Y. Zhou, D. G. Lidzey, T. Wang, *Adv. Mater.* **2017**, 29, 1604044.